

# JMV4851P

## *Product Preview*

**30V 20A P-Channel MOSFET**

**Features**

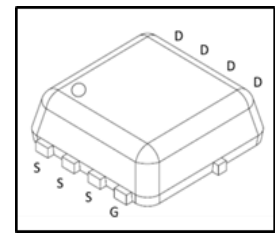
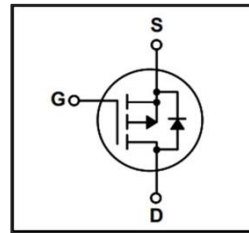
- Advanced trench technology
- Ultra-low on-resistance
- RoHS compliant
- 100% avalanche tested



Product Summary	
$V_{DS}$	-30V
$R_{DS(ON)}$	11 m $\Omega$ (Typ.)
	14.3 m $\Omega$ (Max.)
$I_D$	-20A

**Applications**

- Motor controllers
- DC-to-DC convertors
- Battery-driven electronic products, electrical equipment and machines


**Ordering Information**

Part Number	Marking	Package	Packaging
JMV4851P	V4851P	DFN3.3x3.3	Tape & Reel

**Absolute Maximum Ratings**

Parameter	Symbol	Limit	Unit
Drain-to-Source Voltage	$V_{DS}$	-30	V
Gate-to-Source Voltage	$V_{GS}$	$\pm 20$	
Continuous Drain Current, Package Limited ( $T_C = 25^\circ\text{C}$ ) <sup>(1)</sup>	$I_D$	-20	A
Continuous Drain Current, Silicon Limited ( $T_C = 25^\circ\text{C}$ ) <sup>(1)</sup>	$I_D$	-46	
Continuous Drain Current, Silicon Limited ( $T_C = 100^\circ\text{C}$ ) <sup>(1)</sup>	$I_D$	-29	
Continuous Drain Current, Silicon Limited t ( $T_A = 25^\circ\text{C}$ ) <sup>(2), (5)</sup>	$I_D$	-10	
Continuous Drain Current, Silicon Limited ( $T_A = 100^\circ\text{C}$ ) <sup>(2), (5)</sup>	$I_D$	-6	
Pulsed Drain Current <sup>(3)</sup>	$I_{DM}$	-80	
Power Dissipation ( $T_C = 25^\circ\text{C}$ )	$P_D$	44.6	W
Linear Derating Factor	-	0.36	W/ $^\circ\text{C}$
Single Pulse Avalanche Energy <sup>(4)</sup>	$E_{AS}$	60	mJ
Avalanche Current	$I_{AS}$	25	A
Junction Temperature	$T_J$	-55 to 150	$^\circ\text{C}$
Storage Temperature	$T_{STG}$	-55 to 150	

**Thermal Characteristics**

Parameter	Symbol	Max	Unit
Junction-to-Ambient Thermal Resistance <sup>(5)</sup>	$R_{\theta JA}$	62	$^\circ\text{C}/\text{W}$
Junction-to-Case Thermal Resistance	$R_{\theta JC}$	2.8	

**Static Electrical Characteristics<sup>(6)</sup>**

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-to-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS} = 0\text{V}, I_D = -250\mu\text{A}$	-30	-	-	V
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{DS} = V_{GS}, I_D = -250\mu\text{A}$	-1.0	-	-2.0	
Drain-to-Source Leakage Current	$I_{DSS}$	$V_{DS} = -30\text{V}, V_{GS} = 0\text{V}$	-	-	-1	$\mu\text{A}$
Gate-to-Source Leakage Current	$I_{GSS}$	$V_{DS} = 0\text{V}, V_{GS} = \pm 20\text{V}$	-	-	$\pm 100$	nA
Drain-to-Source On-Resistance	$R_{DS(ON)}$	$V_{GS} = -10\text{V}, I_D = -10\text{A}$	-	11	14.3	$\text{m}\Omega$
		$V_{GS} = -4.5\text{V}, I_D = -10\text{A}$	-	13.5	17.5	$\text{m}\Omega$

**Dynamic Electrical Characteristics <sup>(6)</sup>**

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Forward Transconductance	$g_{fs}$	$V_{DS} = -5V, I_D = -20A$	-	58	-	S
Total Gate Charge	$Q_g$	$V_{GS} = -10V,$	-	40	-	nC
Gate-to-Source Charge	$Q_{gs}$	$V_{DS} = -15V,$	-	5	-	
Gate-to-Drain Charge	$Q_{gd}$	$I_D = -20A$	-	9	-	
Turn-On Delay Time	$t_{d(on)}$	$V_{GS} = -10V,$	-	5	-	ns
Rise Time	$t_r$	$V_{DS} = -15V,$	-	10	-	
Turn-Off Delay Time	$t_{d(off)}$	$I_D = -20A,$	-	50	-	
Fall Time	$t_f$	$R_G = 3.0\Omega$	-	25	-	
Input Capacitance	$C_{iss}$	$V_{GS} = 0V,$	-	2160	-	pF
Output Capacitance	$C_{oss}$	$f = 200kHz,$	-	130	-	
Reverse Transfer Capacitance	$C_{rss}$	$V_{DS} = -15V$	-	105	-	

**Diode Characteristics <sup>(6)</sup>**

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Forward Voltage	$V_{SD}$	$V_{GS} = 0V, I_S = -10A$	-	-0.9	-	V
Reverse Recovery Time	$t_{rr}$	$V_{GS} = 0V, I_S = -10A,$	-	40	-	ns
Reverse Recovery Charge	$Q_{rr}$	$di_S/dt = -100A/\mu s$	-	40	-	nC

(1) Rated according to  $R_{\theta JC}$ .

(2) Rated according to  $R_{\theta JA}$ .

(3) Limited by maximum  $T_J$ .

(4)  $T_A = 25^\circ C, L = 0.1mH, I_{AS} = 25A$ .

(5) Surface-mounted on 1 inch<sup>2</sup> FR4 board, 2 oz Cu.

(6)  $T_J = 25^\circ C$  unless otherwise specified.

Typical Electrical Characteristics

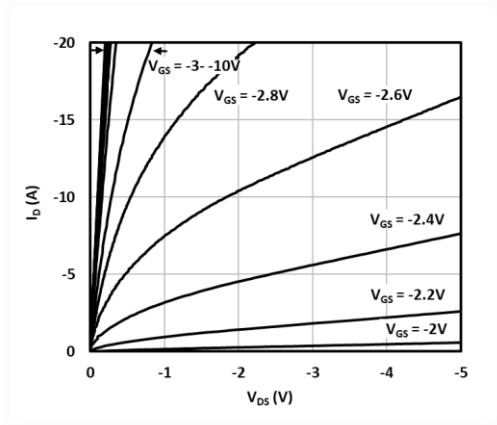


Fig. 1 Output characteristics

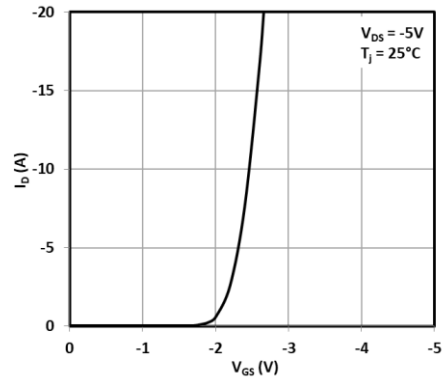


Fig. 2 Transfer characteristics

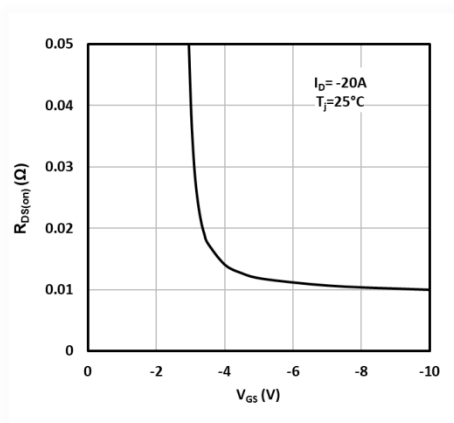


Fig.3 On-resistance vs. gate voltage

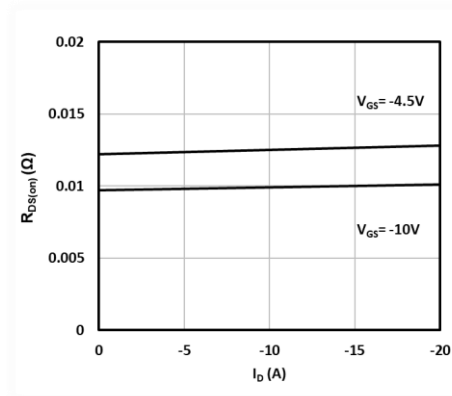


Fig.4 On-resistance vs. drain current

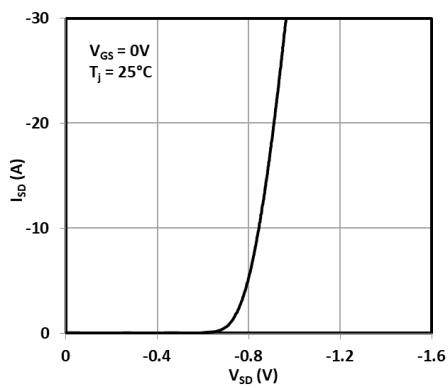


Fig.5 Source-to-drain diode forward characteristics

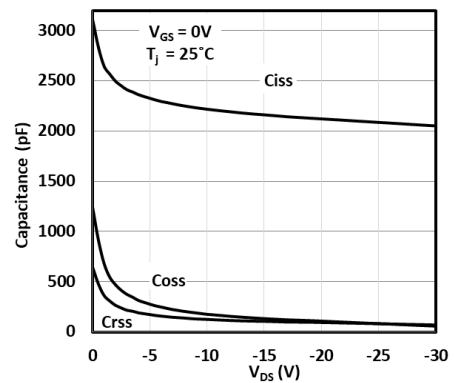
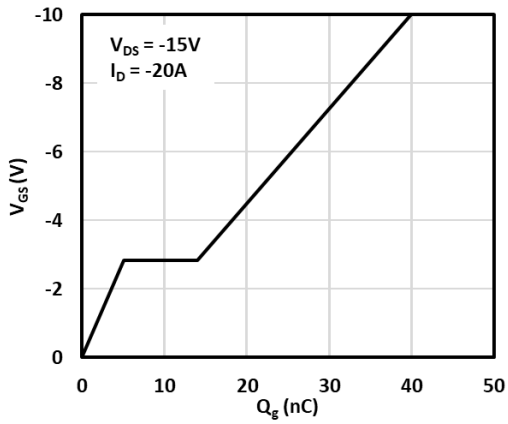
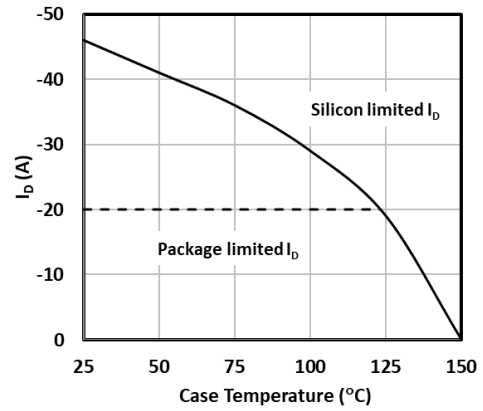


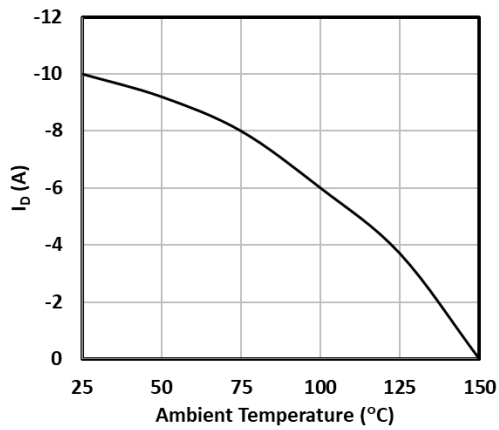
Fig.6 Capacitance vs. drain-to-source voltage



**Fig.7 Gate-to-source voltage vs. gate charge**

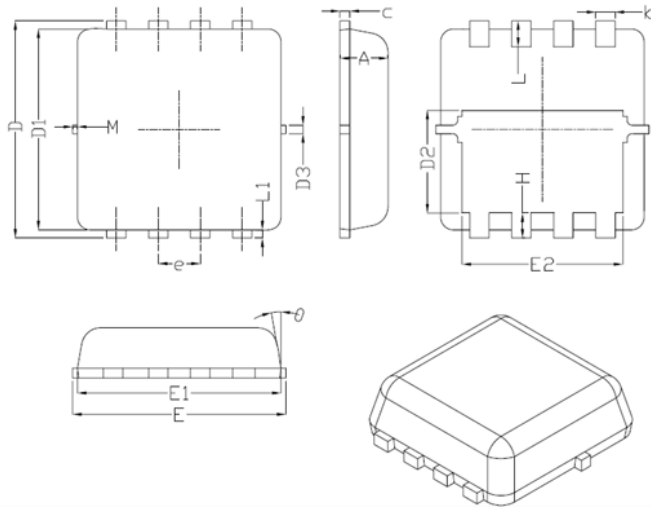


**Fig.8 Maximum drain current vs. case temperature**



**Fig. 9 Maximum drain current vs. ambient temperature**

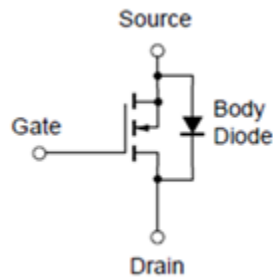
**Package Drawing**



DIM.	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.70	0.80	0.90
b	0.25	0.32	0.39
c	0.10	0.15	0.25
D	3.00	3.30	3.60
D1	3.00	3.10	3.50
D2	1.48	2.00	2.20
D3	--	0.20	--
E	3.00	3.30	3.60
E1	3.00	3.10	3.25
E2	2.29	2.49	2.69
e	0.65 BSC		
H	0.15	0.25	0.50
L	0.15	0.40	0.60
L1	0.05	0.15	0.25
$\alpha$	8°	10°	12°
M	--	0.10	--

**DFN 3.3x3.3**

**Equivalent Circuit**



**Revision history of JMV4851P specification**

<b>Version</b>	<b>Change Items</b>	<b>Effective Date</b>
1.00	Initial Release	28-Feb-20



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